

RoHS Compliant Product
A suffix of "-C" specifies halogen & lead-free

DESCRIPTION

Silicon epitaxial planar

FEATURES

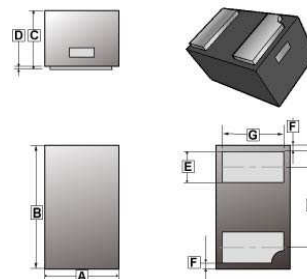
- Small surface mounting type
- Low reverse current and low forward voltage
- High reliability

APPLICATION

High speed switching For Detection

For portable equipment: (i.e. Mobile phone, MP3, MD, CD-ROM, DVD-ROM, Note book PC, etc)

DFNWB



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	0.55	0.65	E	0.15	0.35
B	0.95	1.05	F	0.05REF	
C	0.4	0.5	G	0.4	0.6
D	0	0.05	H	0.65TYP	

MARKING :

Cathode - ·5 +Anode

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS at T_A = 25°C

PARAMETER	SYMBOL	RATINGS	UNIT
Peak Reverse Voltage	V _{RM}	40	V
DC Reverse Voltage	V _R	30	V
Mean Rectifying Current	I _o	30	mA
Peak Forward Surge Current	I _{FSM}	150	mA
Junction, Storage Temperature	T _J , T _{STG}	+125, -40 ~ +125	°C

ELECTRICAL RATING at T_A = 25°C

PARAMETERS	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
Forward Voltage	V _F			0.37	V	I _F = 1mA
Reverse Current	I _R			0.5	μA	V _R = 30V
Capacitance between terminals	C _T		2		pF	V _R = 30V, f = 1MHZ

RATINGS AND CHARACTERISTIC CURVES

● **Electrical characteristic curves ($T_a = 25^\circ\text{C}$)**

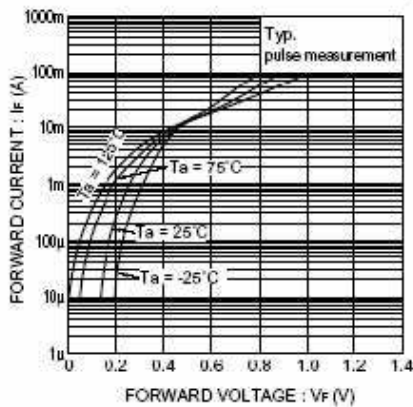


Fig. 1 Forward characteristics

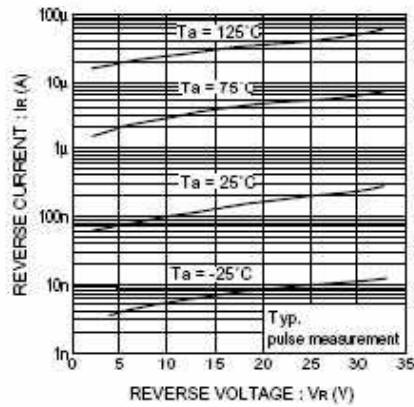


Fig. 2 Reverse characteristics

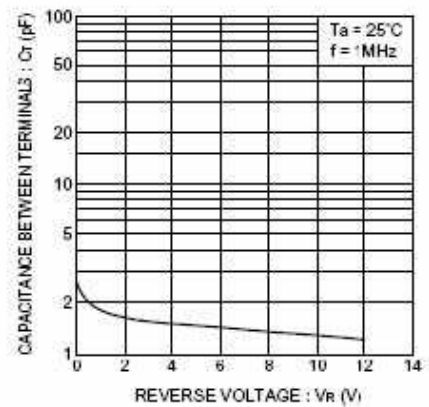


Fig. 3 Capacitance between terminals characteristics